

MC100EP11DR2GH Datasheet



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DiGi Electronics Part Number MC100EP11DR2GH-DG

Manufacturer onsemi

Manufacturer Product Number MC100EP11DR2GH

Description IC CLK BUFFER 1:2 3GHZ 8SOIC

Detailed Description Clock Fanout Buffer (Distribution) IC 1:2 3 GHz 8-SO

IC (0.154", 3.90mm Width)



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MC100EP11DR2GH	onsemi
Series:	Product Status:
100EP	Obsolete
Type:	Number of Circuits:
Fanout Buffer (Distribution)	1
Ratio - Input:Output:	Differential - Input:Output:
1;2	Yes/Yes
Input:	Output:
ECL, PECL	ECL, PECL
Frequency - Max:	Voltage - Supply:
3 GHz	3V ~ 5.5V
Operating Temperature:	Mounting Type:
-40°C ~ 85°C	Surface Mount
Package / Case:	Supplier Device Package:
8-SOIC (0.154", 3.90mm Width)	8-SOIC
Base Product Number:	
MC100EP11	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FΔRQQ	8542 39 0001





3.3 V/5 V ECL 1:2 Differential Fanout Buffer MC10EP11, MC100EP11

Description

The MC10/100EP11 is a differential 1:2 fanout buffer. The device is pin and functionally equivalent to the LVEL11 device. With AC performance much faster than the LVEL11 device, the EP11 is ideal for applications requiring the fastest AC performance available.

The 100 Series contains temperature compensation.

Features

- 220 ps Typical Propagation Delay
- Maximum Clock Frequency > 3 GHz Typical
- PECL Mode Operating Range:
- $V_{CC} = 3.0 \text{ V}$ to 5.5 V with $V_{EE} = 0 \text{ V}$
- NECL Mode Operating Range:
 - $V_{CC} = 0 \text{ V}$ with $V_{EE} = -3.0 \text{ V}$ to -5.5 V
- Open Input Default State
- Safety Clamp on Inputs
- Q Outputs Will Default LOW with Inputs Open or at V_{EE}
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant









SOIC-8 NB D SUFFIX CASE 751-07

TSSOP-8 DT SUFFIX CASE 948R-02

DFN-8 MN SUFFIX CASE 506AA

MARKING DIAGRAM











H = MC10 K = MC100 2Z = MC100 M = Date Code

A = Assembly Location

L = Wafer Lot
Y = Year
W = Work Week
= Pb-Free Package

(Note: Microdot may be in either location)

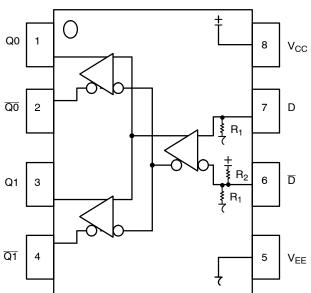
*For additional marking information, refer to Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

NOTE: Some of the device on this data sheet have been **DISCONTINUED**. Please refer to the table on page 8.

1



exposed pad must be connected to a sufficient thermal conduit. Electrically

Table 1. PIN DESCRIPTION

FUNCTION

ECL Data Inputs

Positive Supply

Negative Supply

ECL Data Outputs

(DFN-8 only) Thermal

connect to the most negative supply (GND) or leave unconnected, floating open.

PIN

 V_{CC}

V_{EE} EP

D*, D**

 $Q0, \overline{Q0}, Q1, \overline{Q1}$

- * Pins will default LOW when left open.
- ** Pins will default to high when left open.

Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	37.5 kΩ
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN-8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	73 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	·

^{1.} For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		6	V
V _{EE}	NECL Mode Power Supply	V _{CC} = 0 V	V _{CC} = 0 V		V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$ \begin{array}{l} V_I \leq V_{CC} \\ V_I \geq V_{EE} \end{array} $	6 -6	V
l _{out}	Output Current	Continuous Surge		50 100	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θJA	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θЈС	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
θЈС	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θJΑ	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN-8	129 84	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN-8	35 to 40	°C/W
T _{sol}	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. 10EP DC CHARACTERISTICS, PECL ($V_{CC} = 3.3 \text{ V}$, $V_{EE} = 0 \text{ V}$ (Note 1))

		−40°C			25°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Negative Power Supply Current	20	29	37	20	30	39	22	31	40	mA
V _{OH}	Output HIGH Voltage (Note 2)	2165	2290	2415	2230	2355	2480	2290	2415	2540	mV
V _{OL}	Output LOW Voltage (Note 2)	1365	1490	1615	1430	1555	1680	1490	1615	1740	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2090		2415	2155		2480	2215		2540	mV
V _{IL}	Input LOW Voltage (Single-Ended)	1365		1690	1430		1755	1490		1815	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		3.3	2.0		3.3	2.0		3.3	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.3 V to -2.2 V.
 All loading with 50 Ω to V_{CC} 2.0 V.
 V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

^{1.} JEDEC standard multilayer board - 2S2P (2 signal, 2 power).

Table 5. 10EP DC CHARACTERISTICS, PECL (V_{CC} = 5.0 V, V_{EE} = 0 V (Note 1))

			-40°C			25°C			85°C		Unit
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Negative Power Supply Current	20	29	37	20	30	39	22	31	40	mA
V _{OH}	Output HIGH Voltage (Note 2)	3865	3990	4115	3930	4055	4180	3990	4115	4240	mV
V _{OL}	Output LOW Voltage (Note 2)	3065	3190	3315	3130	3255	3380	3190	3315	3440	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	3790		4115	3855		4180	3915		4240	mV
V _{IL}	Input LOW Voltage (Single-Ended)	3065		3390	3130		3455	3190		3515	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		5.0	2.0		5.0	2.0		5.0	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC}. 2. All loading with 50 Ω to V_{CC} 2.0 V.
- 3. VIHCMR min varies 1:1 with VEE, VIHCMR max varies 1:1 with VCC. The VIHCMR range is referenced to the most positive side of the differential input signal.

Table 6. 10EP DC CHARACTERISTICS, NECL ($V_{CC} = 0 \text{ V}$; $V_{EE} = -5.5 \text{ V}$ to -3.0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Negative Power Supply Current	20	29	37	20	30	39	22	31	40	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1135	-1010	-885	-1070	-945	-820	-1010	-885	-760	mV
V _{OL}	Output LOW Voltage (Note 2)	-1935	-1810	-1685	-1870	-1745	-1620	-1810	-1685	-1560	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1210		-885	-1145		-820	-1085		-760	mV
V _{IL}	Input LOW Voltage (Single-Ended)	-1935		-1610	-1870		-1545	-1810		-1485	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	V _{EE}	+ 2.0	0.0	V _{EE} ·	+ 2.0	0.0	V _{EE}	+ 2.0	0.0	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC}. 2. All loading with 50 Ω to V_{CC} 2.0 V.
- V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 7. 100EP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{EE} = 0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Negative Power Supply Current	26	35	44	26	35	44	26	35	46	mA
V _{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V _{OL}	Output LOW Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
V _{IL}	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		3.3	2.0		3.3	2.0		3.3	٧
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.3 V to -2.2 V.
- 2. All loading with 50 Ω to V_{CC} 2.0 V.
- 3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 8. 100EP DC CHARACTERISTICS, PECL ($V_{CC} = 5.0 \text{ V}$, $V_{EE} = 0 \text{ V}$ (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Negative Power Supply Current	26	35	44	26	35	44	26	35	46	mA
V _{OH}	Output HIGH Voltage (Note 2)	3855	3980	4105	3855	3980	4105	3855	3980	4105	mV
V _{OL}	Output LOW Voltage (Note 2)	3055	3180	3305	3055	3180	3305	3055	3180	3305	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	3775		4120	3775		4120	3775		4120	mV
V _{IL}	Input LOW Voltage (Single-Ended)	3055		3375	3055		3375	3055		3375	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		5.0	2.0		5.0	2.0		5.0	٧
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +2.0 V to -0.5 V.
- 2. All loading with 50 Ω to V_{CC} 2.0 V. 3. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 9. 100EP DC CHARACTERISTICS, NECL (V_{CC} = 0 V; V_{EE} = -5.5 V to -3.0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Negative Power Supply Current	26	35	44	26	35	44	26	35	46	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V _{OL}	Output LOW Voltage (Note 2)	-1945	-1820	-1695	-1945	-1820	-1695	-1945	-1820	-1695	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1225		-880	-1225		-880	-1225		-880	mV
V _{IL}	Input LOW Voltage (Single-Ended)	-1945		-1625	-1945		-1625	-1945		-1625	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	V _{EE}	+ 2.0	0.0	V _{EE}	+ 2.0	0.0	V _{EE}	+ 2.0	0.0	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 –150			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC}.
- 2. All loading with 50 Ω to V_{CC} 2.0 V.
- V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 10. AC CHARACTERISTICS ($V_{CC} = 0 \text{ V}$; $V_{EE} = -3.0 \text{ V}$ to -5.5 V or $V_{CC} = 3.0 \text{ V}$ to 5.5 V; $V_{EE} = 0 \text{ V}$ (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Frequency (Figure 2)		> 3			> 3			> 3		GHz
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential CLK to Q, Q	140	200	250	160	220	270	180	240	300	ps
t _{SKEW}	Within Device Skew Q0, Q1 (Note 2) Device-to-Device Skew		10	15 110		15	20 110		20	25 120	ps
t _{JITTER}	Random Clock Jitter (RMS) (Figure 2)		0.2	< 1		0.2	< 1		0.2	< 1	ps
V _{INPP}	Input Voltage Swing Sensitivity (Differential Configuration)	150	800	1200	150	800	1200	150	800	1200	mV
t _r	Output Rise/Fall Times Q, Q (20% – 80%) @ 1.0 GHz	70	120	170	80	130	180	90	150	200	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} 2.0 V.
- 2. Skew is measured between outputs under identical transitions. Duty cycle skew is defined only for differential operation when the delays are measured from the cross point of the inputs to the cross point of the outputs.

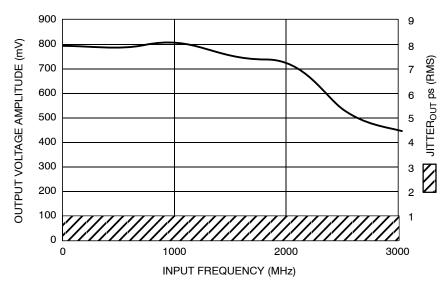


Figure 2. Output Voltage Amplitude (V_{OUTPP}) RMS Jitter vs. Input Clock Frequency at Ambient Temperature

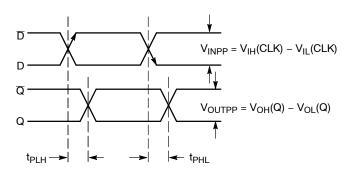


Figure 3. AC Reference Measurement

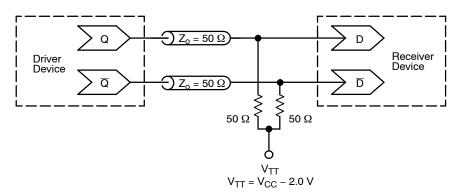


Figure 4. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10EP11DG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC10EP11DR2G	SOIC-8 NB (Pb-Free)	2500 / Tape & Reel
MC100EP11DG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC100EP11DR2G	SOIC-8 NB (Pb-Free)	2500 / Tape & Reel
MC100EP11DTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100EP11DTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel
MC100EP11MNR4G	DFN-8 (Pb-Free)	1000 / Tape & Reel

DISCONTINUED (Note 3)

Device	Package	Shipping [†]
MC10EP11DTG	TSSOP-8 (Pb-Free)	100 Units / Tube

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AN1672/D - The ECL Translator Guide

AND8001/D - Odd Number Counters Design

AND8002/D - Marking and Date Codes

AND8020/D - Termination of ECL Logic Devices

AND8066/D - Interfacing with ECLinPS

AND8090/D - AC Characteristics of ECL Devices

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^{3.} **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.



MECHANICAL CASE OUTLINE

DIMENSIONING AND TOLERANCING PER

PAD AS WELL AS THE TERMINALS.

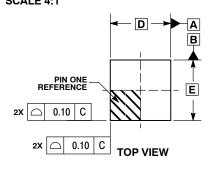
ASME Y14.5M, 1994 . CONTROLLING DIMENSION: MILLIMETERS. DIMENSION 6 APPLIES TO PLATED
TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. COPLANARITY APPLIES TO THE EXPOSED

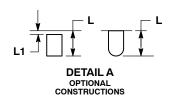
PACKAGE DIMENSIONS

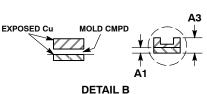


DFN8 2x2, 0.5P CASE 506AA ISSUE F

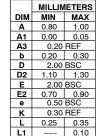
DATE 04 MAY 2016



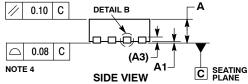




ALTERNATE CONSTRUCTIONS



NOTES



RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

DETAIL A +D2 → 0.10 CAB Ф е С 0.05 NOTE 3

BOTTOM VIEW

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Device

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON18658D	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"	
DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITCH		PAGE 1 OF 1

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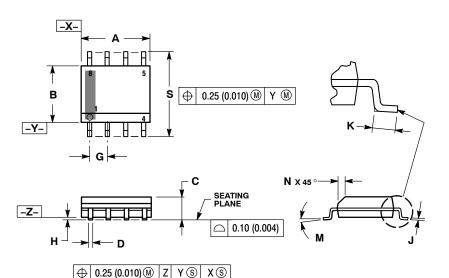
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOIC-8 NB CASE 751-07 **ISSUE AK**

DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		MILLIMETERS INCHES		HES
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27 BSC		0.050 BSC		
Н	0.10 0.25		0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

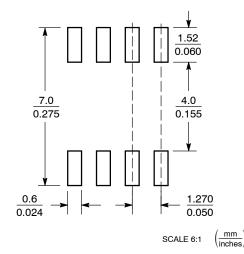
XXXXXX

AYWW

Discrete

H \mathbb{H}

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week = Pb-Free Package XXXXXX = Specific Device Code = Assembly Location Α ww = Work Week = Pb-Free Package

XXXXXX

AYWW

Discrete

(Pb-Free)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2

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SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON STYLE 19:	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN 8. DRAIN
3. V10UT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	7. DHAIN 1 8. MIRROR 1 STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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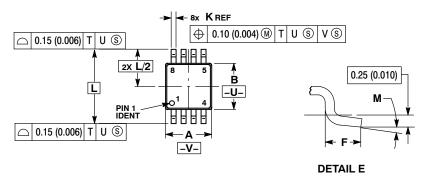
MECHANICAL CASE OUTLINE

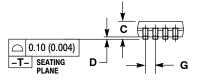
PACKAGE DIMENSIONS

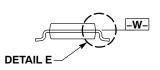


TSSOP-8 3.00x3.00x0.95 CASE 948R-02 **ISSUE A**

DATE 07 APR 2000







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH.
 DIMENSION OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026	BSC
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193	BSC
M	0°	6 °	0°	6°

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